DIODE MODULE

DD(KD)100HB120/160







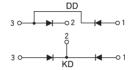
UL;E76102 (M)

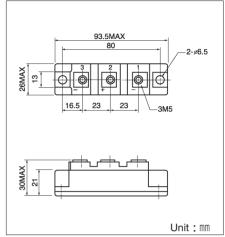
Power Diode Module **DD100HB** series are designed for various rectifier circuits. **DD100HB** has two diode chips connected in series and the mounting base is elctrically isolated from elements for simple heatsink construction. Wide voltage rating up to, 1,600V is avaiable for various input voltage.

- Isolated mounting base
- Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability

(Applications)

Various rectifiers, Battery chargers, DC motor drives





■Maximum Ratings

(Tj=25°C)

Symbol	Itam	Ratings		
	Item	DF100HB120	DD100HB160	Unit
VRRM	Repetitive Peak Reverse Voltage	1200	1600	V
VRSM	Non-Repetitive Peak Reverse Voltage	1350	1700	V

Symbol	li	tem	Conditions	Ratings	Unit
IF (AV)	Average Forward Current		Single phase, half wave, 180° conduction, Tc: 111°C	100	Α
IF (RMS)	R.M.S. Forward Current		Single phase, half wave, 180° conduction, Tc: 111℃	155	Α
IFSM	Surge Forward Current		½ cycle, 50/60Hz, peak value, non-repetitive	1800/2000	Α
l²t	l²t		Value for one cycle of surge current	16500	A ² S
Tj	Junction Temperature			− 40∼ + 150	°C
Tstg	Storage Temperature			− 40∼ + 125	°C
Viso	Isolation Voltage		A.C.1minute	2500	V
	Mounting Torque	Mounting (M6)	Recommended Value 2.5~3.9 (25~40)	4.7 (48)	N ⋅m (kgf ⋅cm)
		Terminal (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	
	Mass			170	g

■Electrical Characteristics

Symbol	Item	Conditions		Unit
IRRM	Repetitive Peak Reverse Current, max.	at VDRM, single phase, half wave. Tj=150°C	30	mA
VFM	Forward Voltage Drop, max.	Foward current 320A, Tj=25°C, Inst. measurement	1.35	V
Rth (j-c)	Thermal Impedance, max.	Junction to case	0.30	°C/W

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